fast SiC semiconductor

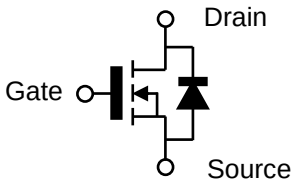
FF06320

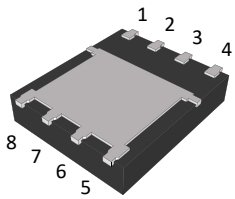
Product Datasheet

Silicon Carbide MOSFET

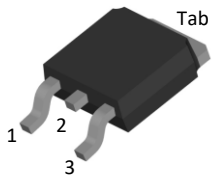
650V, 320mΩ SiC MOSFET – Falcon Series

Product Information:





PQFN 5 x 6



TO-252, DPAK

Features

- Optimized $R_{DS(on)}$ with Rapid Switching Behavior
- Low Profile & Low Parasitic Inductance Packaging
- Compatible with Standard Gate Drivers
- High Avalanche Endurance Capability
- Optimized for High Power Density Applications
- Compact MSL-1 SMT Package
- RoHS Compliant and Halogen Free

Terminal	Packaging Type	
	TO-252-DPAK	PQFN 5x6
Gate	1	4
Drain	2, Tab	5, 6, 7, 8
Source	3	1, 2, 3

Benefits

- Higher System Efficiency
- Increase Parallel Device Convenience
- Enable High Temperature Application
- Allow High Frequency Operation
- Realize Compact and Lightweight Systems
- High Reliability

Potential Applications

- Switching Mode Power Supply
- Power Factor Correction
- Portable Adaptor
- Telecom Power
- Renewable Energy
- Class D amplifier

Key Performance Parameters

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS} @$T_{j(max)}$	750	V
Recommended Gate-Source Turn-On Voltage	V_{GS}	15~18	
Drain-Source On-State Resistance	$R_{DS(on)}$	320	mΩ
Continuous Drain Current	I_D	8.6	A
Pulse Drain Current	$I_{D,\ pulse}$	37	
Power Dissipation	P_{tot}	41	W
Avalanche Energy	E_{AS}	100	mJ
Gate Charge	Q_G	14.5	nC
Output Capacitive Charge	Q_{oss}	12.7	
Junction & Storage Temperature	T_j, T_{stg}	-55 to 175	°C

Part Number	Package	Marking
FF06320A	TO-252, DPAK	FF06320
FF06320B	PQFN 5 x 6	FF06320
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For further information about comparable products, please contact (www.fastsic.com).

Maximum Ratings: (T_j = 25°C, unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Voltage	V_{DSS}	650	--	--	V	V_{GS}=0V, I_D=100μA
Continuous Drain Current	I_D	--	--	8.6 6.3	A	V_{GS}=18V, T_C=25°C V_{GS}=18V, T_C=100°C
Pulse Drain Current	$I_{D,\ pulse}$	--	--	37		Per Fig. 10
Continuous Body Diode Current	I_S	--	--	6.5		V_{GS}=0V, T_C=25°C
Avalanche Energy, Single Pulse	E_{AS}	--	--	100	mJ	L=25mH
Operate Gate Source Voltage	$V_{GS,\ op}$	-3~0	--	15~18	V	Recommended operating values
Transient Gate Source Voltage	$V_{GS,\ tran.}$	-8	--	22		Transient operating limit (AC f > 1Hz, pulse width < 100ns)
Power Dissipation	P_{tot}	--	--	41	W	T_c=25°C
Junction Temperature	T_j	-55	--	175	°C	--
Storage Temperature	T_{stg}	-55	--	175		
Soldering Temperature	T_L	--	--	260		

Electrical Characteristics:

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
DC Characteristics (at T_j = 25°C, unless otherwise specified)						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	650 --	-- 750	-- --	V	V_{GS}=0V, I_D=100μA, T_j=25°C V_{GS}=0V, I_D=100μA, T_j=175°C
Drain-Source On-State Resistance	$R_{DS(on)}$	--	320 370		mΩ	V_{GS}=18V, I_D=2A, T_j=25°C V_{GS}=18V, I_D=2A, T_j=100°C
Gate-Source Threshold Voltage	V_{th}		1.6		V	V_{GS}=V_{DS} ,I_D=4mA
Zero Gate Voltage Drain Current	I_{DSS}	--	1		μA	V_{DS}=650V, V_{GS}=0V, T_j=25°C V_{DS}=650V, V_{GS}=0V, T_j=175°C
Gate-Source Leakage Current	I_{GSS}	--	--	100	nA	V_{GS}=18V, V_{DS}=0V
Internal Gate Resistance	$R_{G,\ int.}$	--	10	--	Ω	f=1MHz, V_{AC}=25mV
Body Diode Forward Voltage	V_{SD}	--	2.45 2.05		V	V_{GS}=0V, I_S=1A, T_j=25°C V_{GS}=0V, I_S=1A, T_j=175°C
AC Characteristics (at T_j = 25°C, unless otherwise specified)						
Input Capacitance	C_{iss}	--	317.5	--	pF	V_{DS}=400V, V_{GS}=0V, f=250kHz, V_{AC}=25mV
Output Capacitance	C_{oss}	--	22.8	--		
Reverse Capacitance	C_{rss}	--	3.8	--		
Effective Output Capacitance, energy related	$C_{o(er)}$[1]	--	24.9	--		
Effective Output Capacitance, time related	$C_{o(tr)}$[2]	--	31.9	--		
C_{oss} Stored Energy	E_{oss}	--	2.0	--	μJ	
Output Capacitive Charge	Q_{oss}	--	12.7	--	nC	

[1] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V.
[2] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V.

Switching Characteristics:

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Gate Characteristics						
Gate to Source Charge	Q_{GS}	--	2.3	--	nC	V_{DS}=400V, V_{GS}=0V/15V, I_D=2A
Gate to Drain Charge	Q_{GD}	--	7	--		
Total Gate Charge	Q_G	--	14.5	--		
Inductive Load						
Turn On Delay Time	$t_{d(on)}$	--	15.2	--	ns	V_{DS}=400V, I_D=5A, V_{GS}=-3/+15V, $R_{G,ext.}$= 2.7Ω
Rise Time	t_r	--	24.1	--		
Turn Off Delay Time	$t_{d(off)}$	--	19.1	--		
Fall Time	t_f	--	16.8	--		
Resistive Load						
Turn On Delay Time	$t_{d(on)}$	--	9.6	--	ns	V_{DS}=400V, I_D=2A, V_{GS}=-3/+15V, $R_{G,ext.}$= 2.7Ω, R_L=200Ω,
Rise Time	t_r	--	10.7	--		
Turn Off Delay Time	$t_{d(off)}$	--	29.8	--		
Fall Time	t_f	--	38.2	--		
Body Diode Characteristics						
Reverse Recovery Charge	Q_{rr}	--	8.8	--	nC	V_{GS}=0V, I_S=2A, V_{DS}=400V, di/dt=300A/μs *Q_{rr} herein excluded the Q_{oss} value.
Reverse Recovery Time	t_{rr}	--	46	--	ns	
Peak Reverse Recovery Current	I_{rrm}	--	1.1	--	A	

Thermal Characteristics:

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Thermal Impedance, junction-case	$R_{th\text{-}jc}$	--	3.65		K/W	--
Thermal Impedance, junction-ambient	$R_{th\text{-}ja}$	--				Device on PCB, with 6 cm² of cooling area

Electrical Characteristics Diagrams

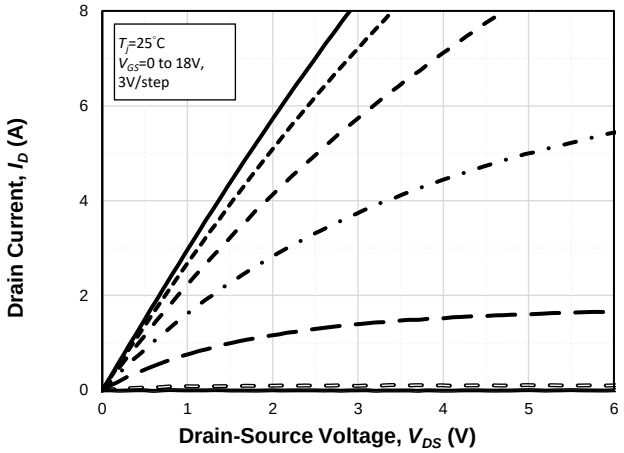


Fig. 1 Typical Output Characteristics at T_j=25˚C

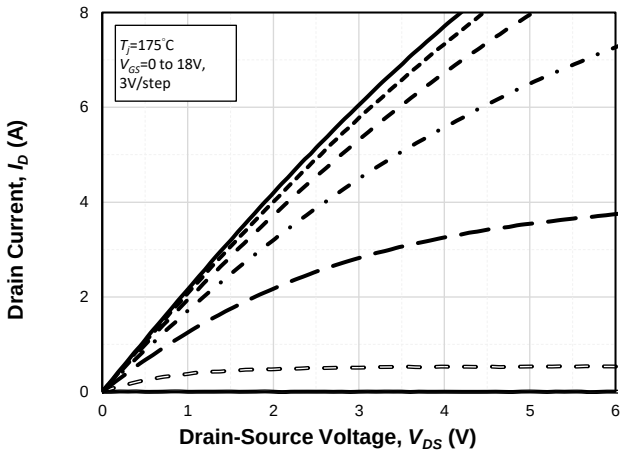


Fig. 2 Typical Output Characteristics at T_j=175˚C

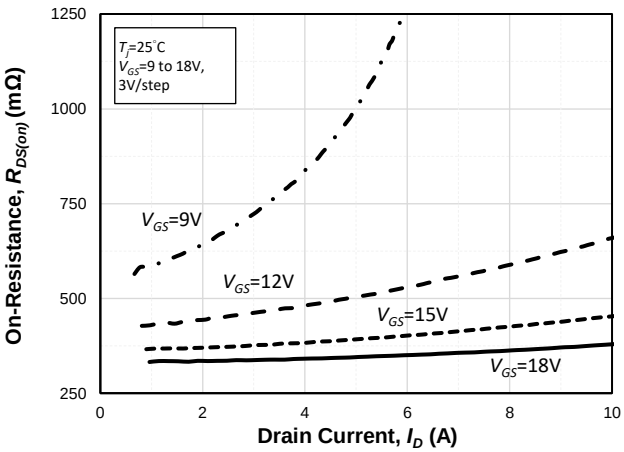


Fig. 3 Typ. $R_{DS(on)}$ vs. I_D with Various V_{GS}

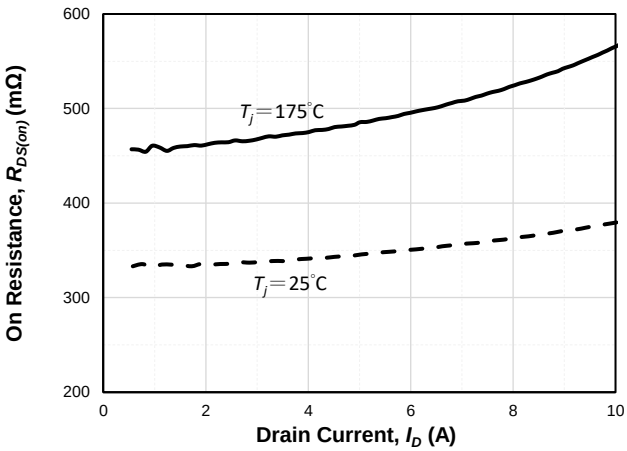


Fig. 4 Typ. $R_{DS(on)}$ vs. I_D with Various T_j, V_{GS}=18V

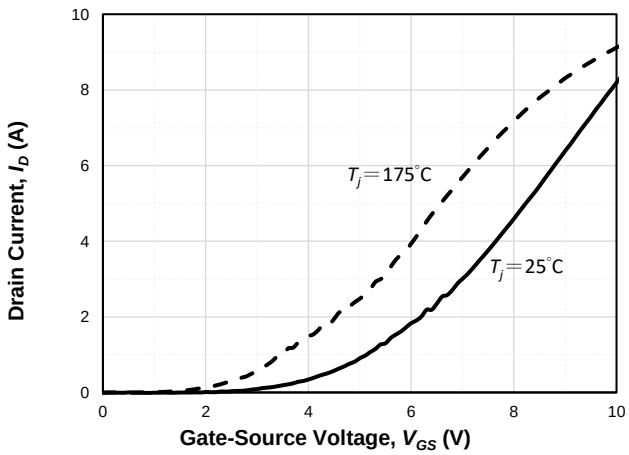


Fig. 5 Typ. I_D vs. V_{GS} with Various T_j, V_{DS}=10V

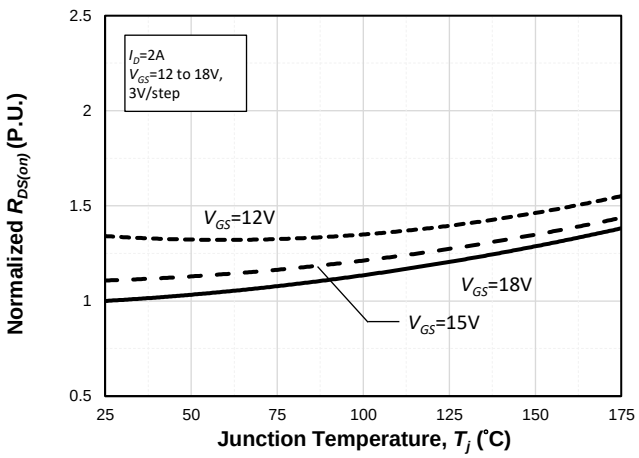


Fig. 6 Normalized $R_{DS(on)}$ vs. T_j with Various V_{GS}

Electrical Characteristics Diagrams

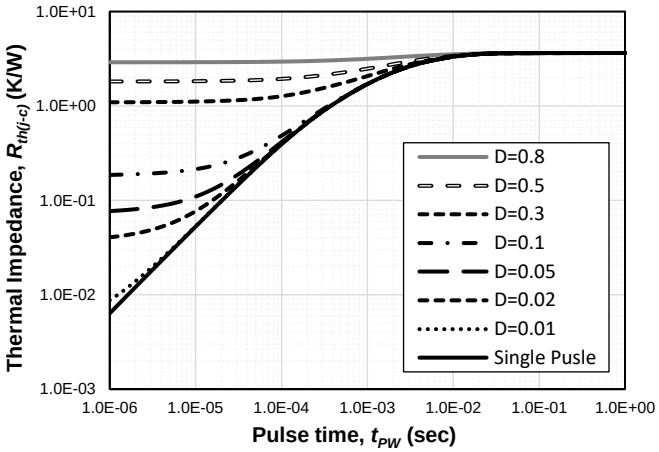


Fig. 7 Typ. Transient Thermal Impedance $R_{th\text{-}jc}$

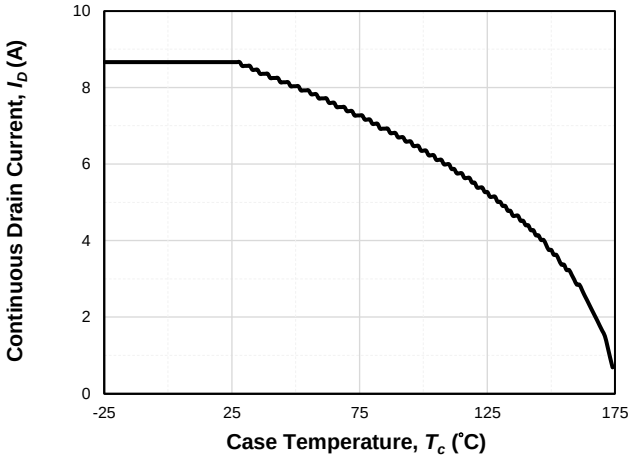


Fig. 8 Continuous I_D De-rating at V_{GS}=18V, T_j≤175˚C

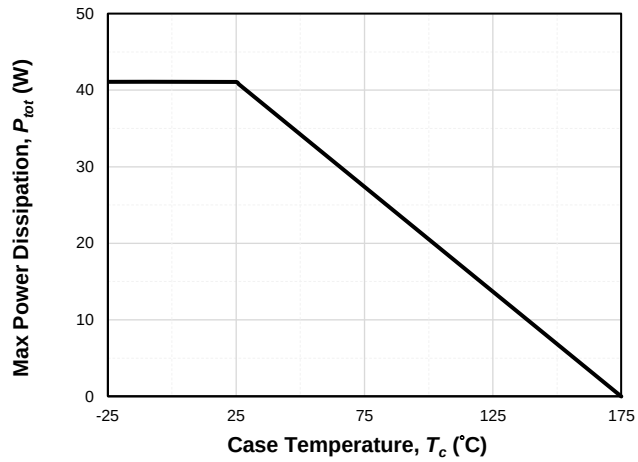


Fig. 9 Power Dissipation at V_{GS}=18V, T_j≤175˚C

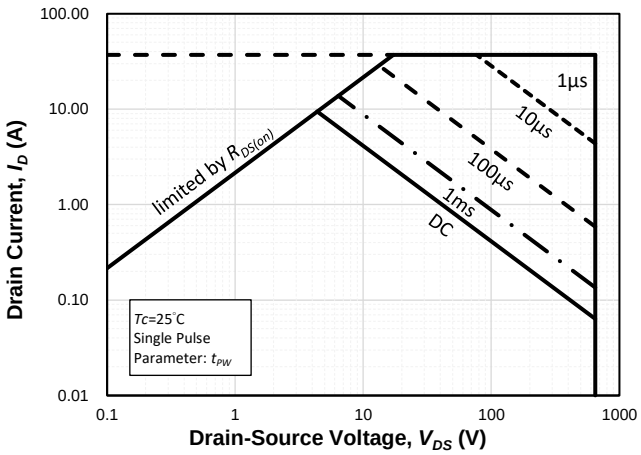


Fig. 10 Safe Operating Area at T_c=25˚C

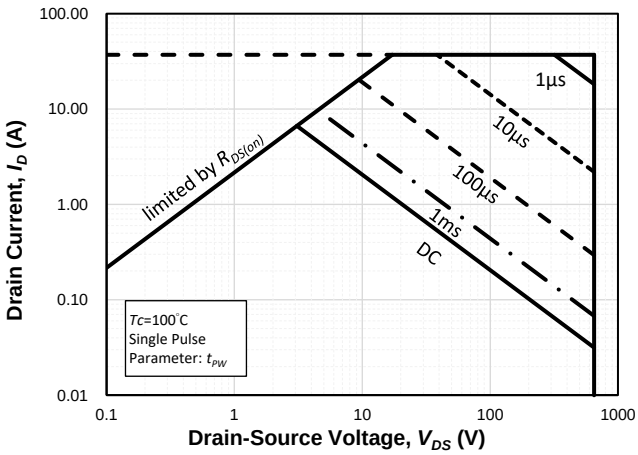


Fig. 11 Safe Operating Area at T_c=100˚C

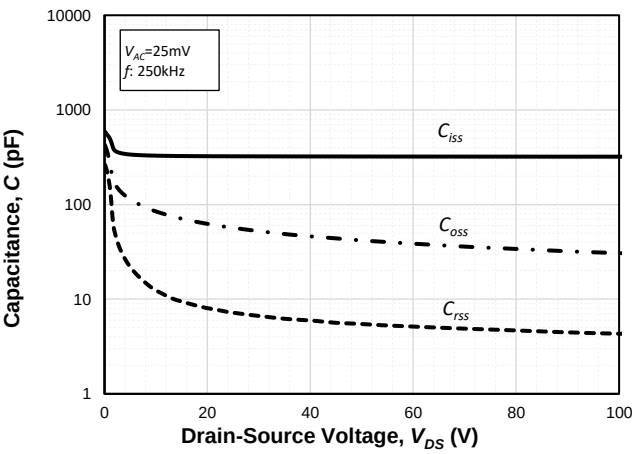


Fig. 12 Typ. Capacitance vs. V_{DS} at f_{sw}=250kHz, V_{DS}≤100V

Electrical Characteristics Diagrams

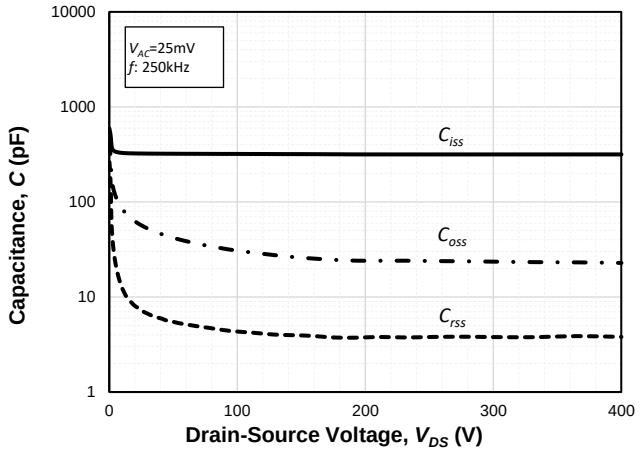


Fig. 13 Typ. Capacitance vs. V_{DS} at f_{sw}=250kHz, V_{DS}≤400V

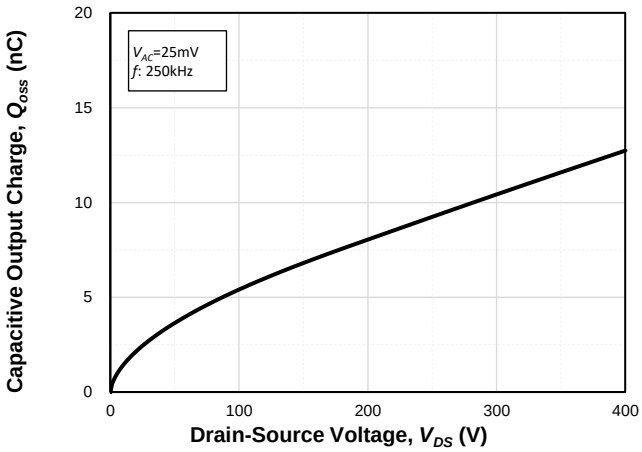


Fig. 14 Typ. Capacitive Output Charge at f_{sw}=250kHz

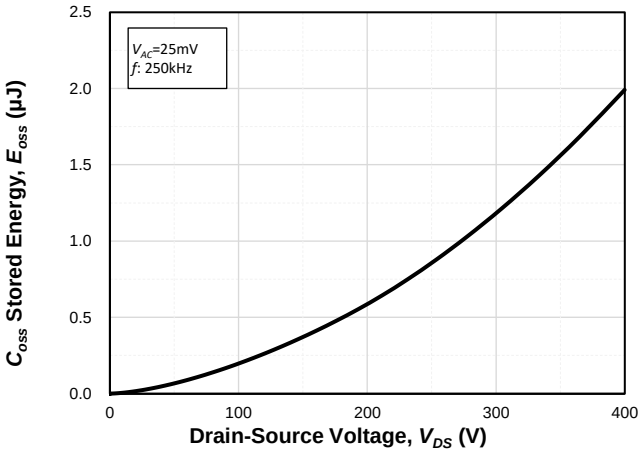


Fig. 15 Typ. C_{oss} Stored Energy at f_{sw}=250kHz

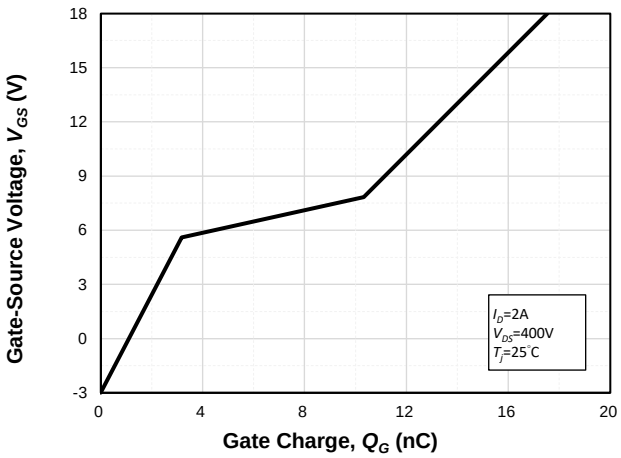


Fig. 16 Typ. Gate Charge at V_{DS}=400V, I_D=2A

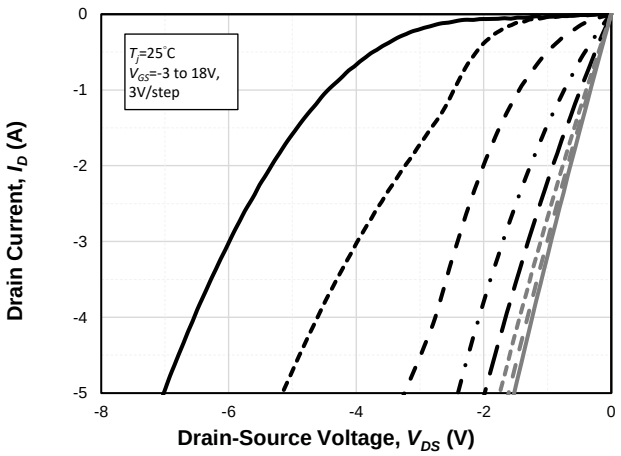


Fig. 17 Typical Forward Characteristics of Reverse Conduction at T_j=25˚C

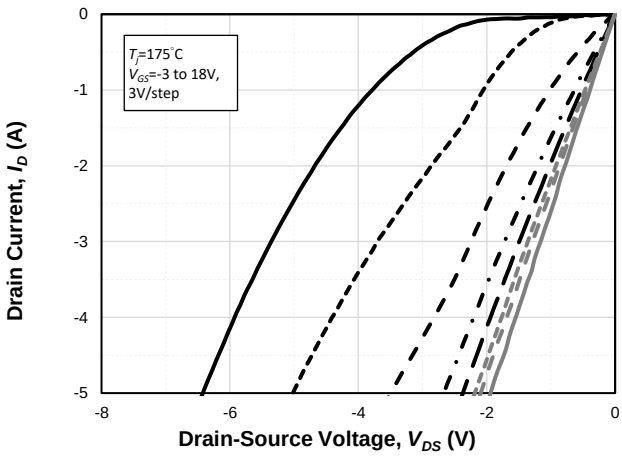


Fig. 18 Typical Forward Characteristics of Reverse Conduction at T_j=175˚C

Electrical Characteristics Diagrams

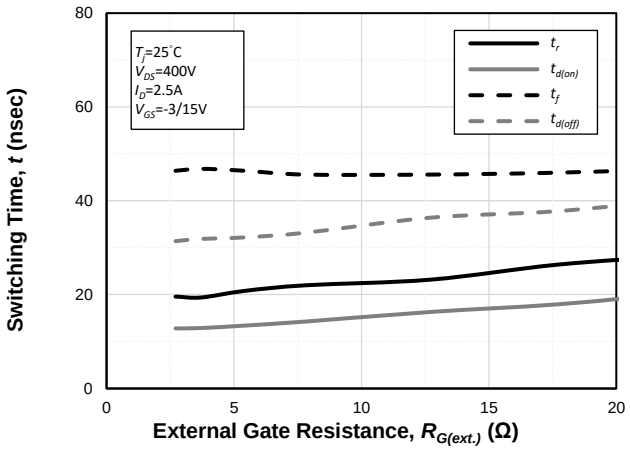


Fig. 19 Typ. Switching Time vs. $R_{G(ext.)}$

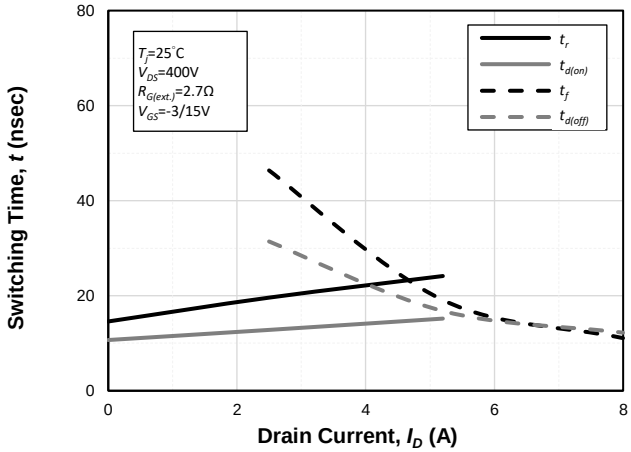


Fig. 20 Typ. Switching Time vs. I_D

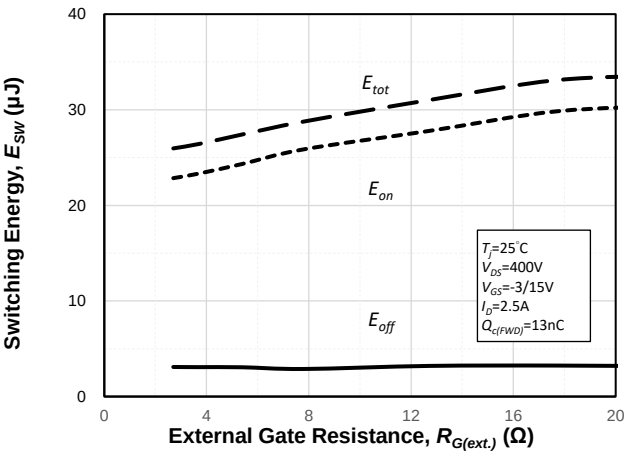


Fig. 21 Typ. Switching Energy vs. $R_{G(ext.)}$

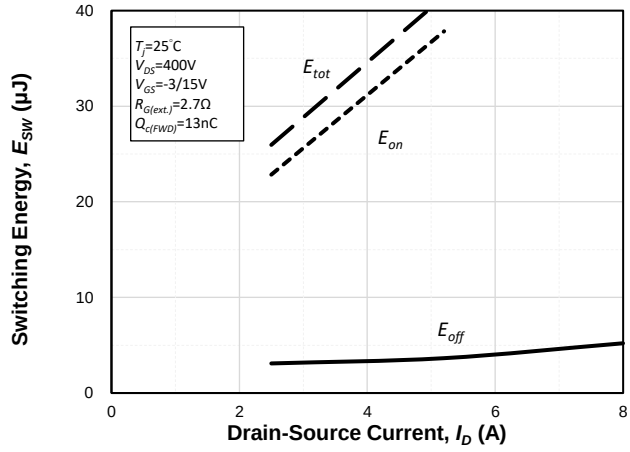


Fig. 22 Typ. Switching Energy vs. I_D

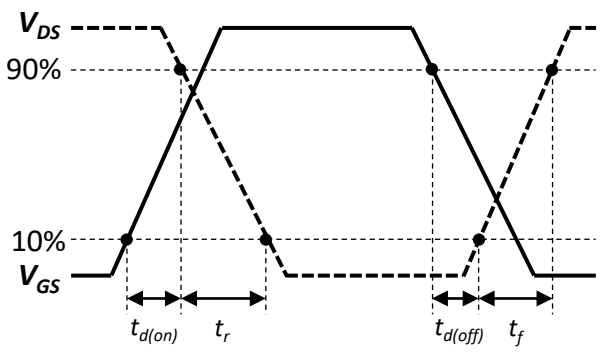


Fig. 23 Definition of Switching Times Waveform

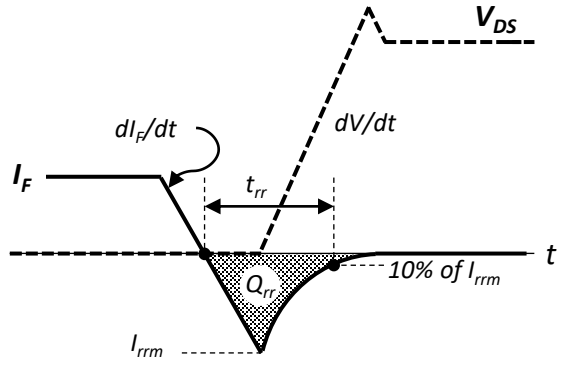
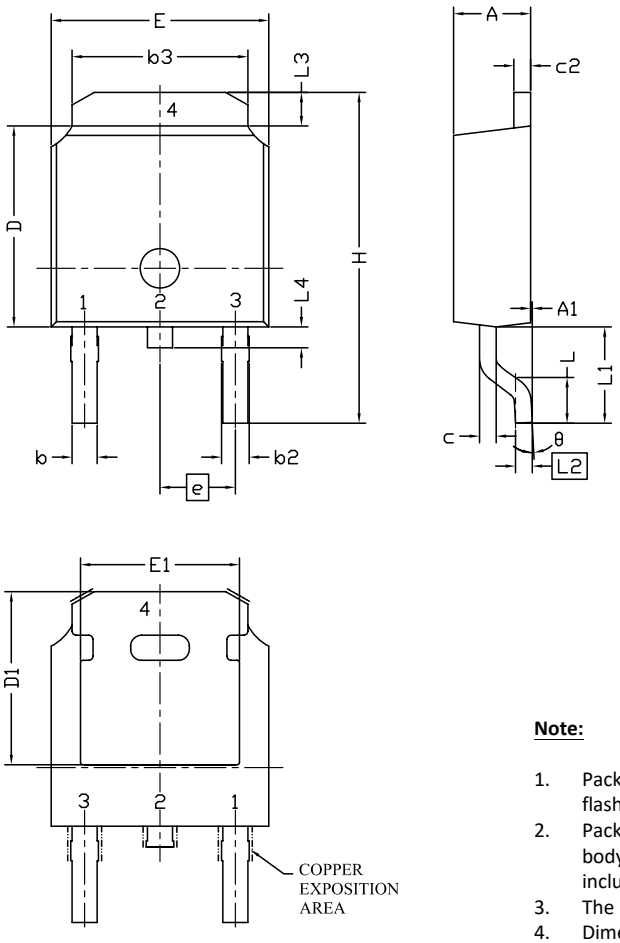


Fig. 24 Definition of Diode Recovery Waveform

Package Outline (TO-252, DPAK)

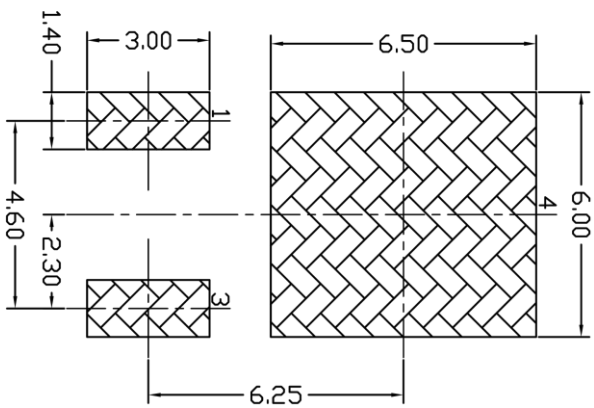


Symbol	Dimension (Millimeters)		
	Min.	Nom.	Max.
E	6.40	6.60	6.73
L	1.40	1.52	1.77
L1		2.743 REF.	
L2		0.508 BSC.	
L3	0.89	--	1.27
L4	0.64	--	1.01
D	6.00	6.10	6.22
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e		2.286 BSC.	
A	2.20	2.30	2.38
A1	0.00	--	0.127
c	0.46	0.50	0.60
c2	0.46	0.50	0.58
D1	5.21	--	--
E1	4.40	--	--
θ	0°	--	10°

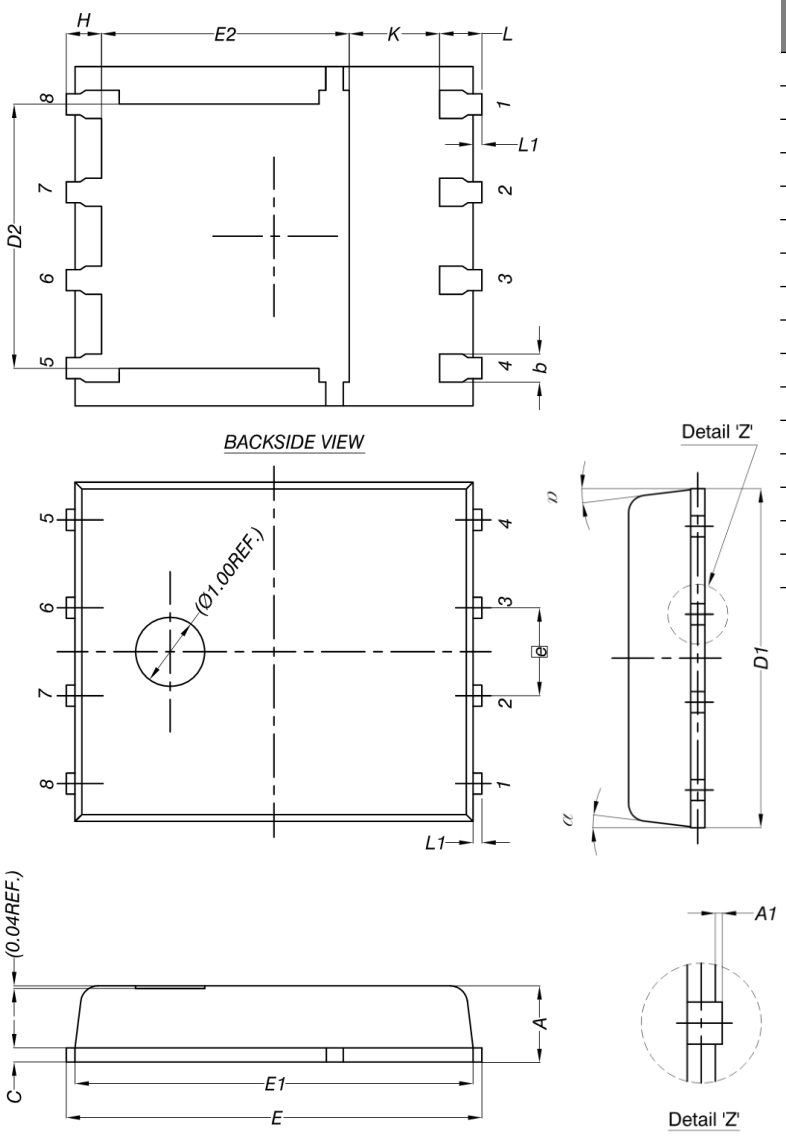
Note:

1. Package body sizes exclude mold flash, protrusion, or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 0.10 mm per side.
2. Package body sizes determined at the outermost extremes of the plastic body exclusive of mold flash, gate burrs, and inter-lead flash, but including any mismatch between the top and bottom of the plastic body.
3. The package top may be smaller than the package bottom.
4. Dimension “b” does not include dambar protrusion. Allowable dambar protrusion shall be 0.10 mm total in excess of “b” dimension at the maximum material condition. The dambar cannot be located on the lower radius of the foot.

Land Pattern (Only for Reference)



Package Outline (PQFN 5 x 6)

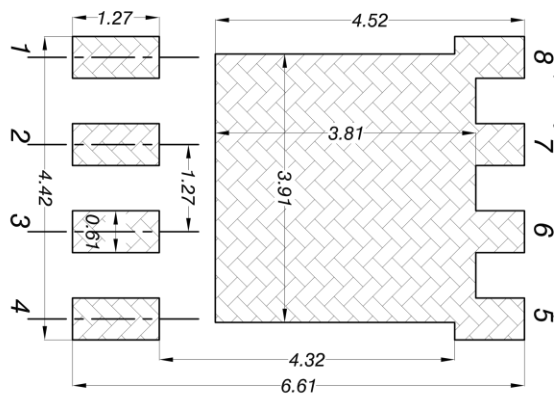


Symbol	Dimension (Millimeters)		
	Min.	Nom.	Max.
A	0.90	1.00	1.10
A1	0	--	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC.		
H	0.41	0.51	0.61
K	1.10	--	--
L	0.51	0.61	0.71
L1	0.06	0.13	020
α	0°	--	12°

Note:

1. Package body sizes exclude mold flash, protrusion, or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 0.10 mm per side
2. Package body sizes determined at the outermost extremes of the plastic body exclusive of mold flash, tie bar, tie bar burrs, gate burrs, and inter-lead flash, but including any mismatch between the top and bottom of the plastic body.
3. The package top may be smaller than the package bottom.

Land Pattern (Only for Reference)



Revision History

Date	Revision	Changes
21.06	Preliminary	1st issue

Important Note (Disclaimer)

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This product is not designed or intended for use for applications in which the failure of the product could lead to personal injury, death or property damage, including but not limited to equipment used in medical systems, traffic communication or control systems, transportations (cars, ships, trains) and aerospace. FSS shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions provided herein.

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